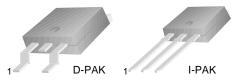


## **MJD117**

### **D-PAK for Surface Mount Applications**

- High DC Current Gain
- Built-in a Damper Diode at E-C
- Lead Formed for Surface Mount Applications (No Suffix)
- Straight Lead (I-PAK, " I " Suffix)
- Electrically Similar to Popular TIP117

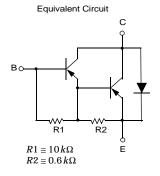


1.Base 2.Collector 3.Emitter

## **PNP Silicon Darlington Transistor**

### Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage	- 100	V	
V <sub>CEO</sub>	Collector-Emitter Voltage - 100		V	
V <sub>EBO</sub>	Emitter-Base Voltage - 5		V	
I <sub>C</sub>	Collector Current (DC)	- 2	Α	
I <sub>CP</sub>	Collector Current (Pulse)	- 4	Α	
I <sub>B</sub>	Base Current	- 50	mA	
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	20	W	
	Collector Dissipation (T <sub>a</sub> =25°C)	1.75	W	
TJ	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C	



### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V <sub>CEO</sub> (sus)	*Collector-Emitter Sustaining Voltage	$I_C = -30 \text{mA}, I_B = 0$	- 100		V
I <sub>CEO</sub>	Collector Cut-off Current	$V_{CE} = -50V, I_{B} = 0$		- 20	μΑ
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -100V, I_{E} = 0$		- 20	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$		- 2	mA
h <sub>FE</sub>	*DC Current Gain	$V_{CE} = -3V, V_{EB} = -0.5A$ $V_{CE} = -3V, V_{EB} = -2A$ $V_{CE} = -3V, I_{C} = -4A$	500 1000 200	12K	
V <sub>CE</sub> (sat)	*Collector-Emitter Saturation Voltage	$I_C = -2A$ , $I_B = -8mA$ $I_C = -4A$ , $I_B = -40mA$		- 2 - 3	V V
V <sub>BE</sub> (sat)	*Base-Emitter Saturation Voltage	I <sub>C</sub> = - 4A, I <sub>B</sub> = - 40mA		- 4	V
V <sub>BE</sub> (on)	*Base-Emitter ON Voltage	V <sub>CE</sub> = - 3A, I <sub>C</sub> = - 2A		- 2.8	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = -10V, I_{C} = -0.75A$	25		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = -10V, I_{E} = 0$ f= 0.1MHz		200	pF

<sup>\*</sup> Pulse Test: PW≤300μs, Duty Cycle≤2%

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# **Typical Characteristics** V<sub>BE</sub>(sat), V<sub>CE</sub>(sat)[V], SATURATION VOLTAGE $V_{CE} = -3V$ I<sub>C</sub> = 250 I<sub>B</sub> hFE, DC CURRENT GAIN I<sub>c</sub>[A], COLLECTOR CURRENT I<sub>c</sub>[A], COLLECTOR CURRENT Figure 1. DC current Gain Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage V<sub>cc</sub>= - 30V Vcc=30V t<sub>STG</sub>, t<sub>F</sub>[μS], TURN OFF TIME $t_{\rm R},\,t_{\rm D}(\mu s),\, {\sf TURN}$ ON TIME I<sub>c</sub>[A], COLLECTOR CURRENT I<sub>C</sub>[A], COLLECTOR CURRENT Figure 3. Collector Output Capacitance Figure 4. Turn On Time Ic[A], COLLECTOR CURRENT C∞[pF], CAPACITANCE -0.01 L -1 $V_{CE}[V]$ , COLLECTOR-EMITTER VOLTAGE $V_{\text{CB}}[V],\, \text{COLLECTOR-BASE}\,\, \text{VOLTAGE}$ Figure 5. Turn Off Time Figure 6. Safe Operating Area

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# Typical Characteristics (Continued)

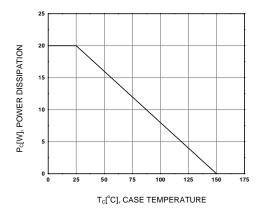
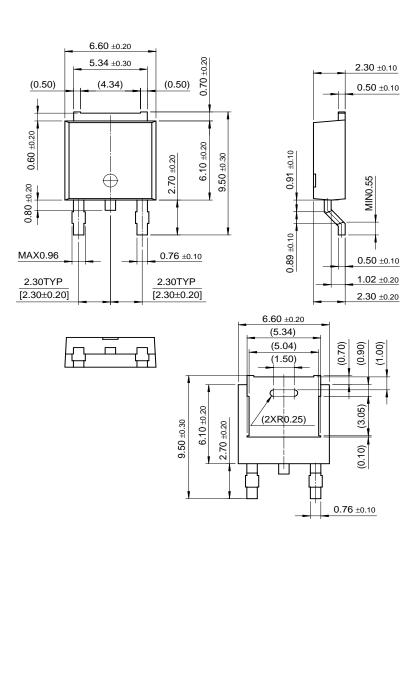


Figure 7. Power Derating

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## **Package Demensions**

## D-PAK



Dimensions in Millimeters

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